# **Quad 3-State Noninverting Buffers**

### **High-Performance Silicon-Gate CMOS**

The MC74HC125A and MC74HC126A are identical in pinout to the LS125 and LS126. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC125A and HC126A noninverting buffers are designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The devices have four separate output enables that are active-low (HC125A) or active-high (HC126A).

#### **Features**

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7A Requirements
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- Pb-Free Packages are Available



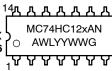
#### ON Semiconductor®

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MARKING DIAGRAMS

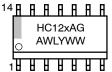


PDIP-14 N SUFFIX CASE 646





SOIC-14 D SUFFIX CASE 751A

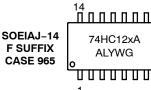




TSSOP-14 DT SUFFIX CASE 948G







A = Assembly Location

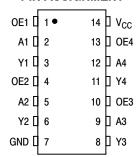
L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G = Pb-Free Package ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### **PIN ASSIGNMENT**



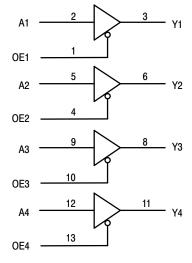
## FUNCTION TABLE

| HC125A |      |        |  |
|--------|------|--------|--|
| In     | outs | Output |  |
| Α      | OE   | Υ      |  |
| Н      | L    | Н      |  |
| L      | L    | L      |  |
| Х      | Н    | Z      |  |

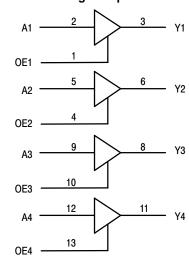
| HC126A |      |        |  |
|--------|------|--------|--|
| Inp    | outs | Output |  |
| Α      | OE   | Υ      |  |
| Н      | Н    | Н      |  |
| L      | Н    | L      |  |
| Х      | L    | Z      |  |

#### **LOGIC DIAGRAM**

## HC125A Active-Low Output Enables



#### HC126A Active-High Output Enables



PIN 14 = V<sub>CC</sub> PIN 7 = GND

#### **MAXIMUM RATINGS**

| Symbol           | Parameter   | Value                    | Unit |
|------------------|---|--------------------------|------|
| V <sub>CC</sub>  | DC Supply Voltage (Referenced to GND)   | - 0.5 to + 7.0           | V    |
| V <sub>in</sub>  | DC Input Voltage (Referenced to GND)  | $-0.5$ to $V_{CC}$ + 0.5 | V    |
| V <sub>out</sub> | DC Output Voltage (Referenced to GND)   | $-0.5$ to $V_{CC}$ + 0.5 | ٧    |
| I <sub>in</sub>  | DC Input Current, per Pin   | ±[ <b>2</b> 0            | mA   |
| I <sub>out</sub> | DC Output Current, per Pin  | ±[ <b>3</b> 5            | mA   |
| Icc              | DC Supply Current, V <sub>CC</sub> and GND Pins   | ±[ <b>7</b> 5            | mA   |
| P <sub>D</sub>   | Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†                | 750<br>500<br>450        | mW   |
| T <sub>stg</sub> | Storage Temperature   | - 65 to + 150            | °C   |
| T <sub>L</sub>   | Lead Temperature, 1 mm from Case for 10 Seconds<br>(Plastic DIP, SOIC or TSSOP Package) | 260                      | °C   |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### RECOMMENDED OPERATING CONDITIONS

| Symbol                             | Parameter  | Min  | Max         | Unit               |    |
|------------------------------------|--|--|-------------|--------------------|----|
| V <sub>CC</sub>                    | DC Supply Voltage (Referenced to GND)                | 2.0  | 6.0         | V                  |    |
| V <sub>in</sub> , V <sub>out</sub> | DC Input Voltage, Output Voltage (Referenced to GND) |  | 0           | V <sub>CC</sub>    | V  |
| T <sub>A</sub>                     | Operating Temperature, All Package Type              | es   | <b>– 55</b> | + 125              | °C |
| t <sub>r</sub> , t <sub>f</sub>    | (Figure 1)   | $V_{CC} = 2.0 \text{ V}$<br>$V_{CC} = 4.5 \text{ V}$<br>$V_{CC} = 6.0 \text{ V}$ | 0           | 1000<br>500<br>400 | ns |

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

|                 |                                  |  |                      | Gu              | aranteed Li    | mit     |      |
|-----------------|----------------------------------|--|----------------------|-----------------|----------------|---------|------|
| Symbol          | Parameter                        | Test Conditions                                  | V <sub>CC</sub><br>V | – 55 to<br>25°C | ≤ <b>85</b> °C | ≤ 125°C | Unit |
| V <sub>IH</sub> | Minimum High-Level Input Voltage | $V_{out} = V_{CC} - 0.1 \text{ V}$               | 2.0                  | 1.5             | 1.5            | 1.5     | V    |
|                 |                                  | $ I_{\text{out}}  \leq 20 \mu\text{A}$           | 3.0                  | 2.1             | 2.1            | 2.1     |      |
|                 |                                  |  | 4.5                  | 3.15            | 3.15           | 3.15    |      |
|                 |                                  |  | 6.0                  | 4.2             | 4.2            | 4.2     |      |
| $V_{IL}$        | Maximum Low-Level Input Voltage  | V <sub>out</sub> = 0.1 V                         | 2.0                  | 0.5             | 0.5            | 0.5     | V    |
|                 |                                  | $ I_{out}  \leq 20 \mu A$                        | 3.0                  | 0.9             | 0.9            | 0.9     |      |
|                 |                                  |  | 4.5                  | 1.35            | 1.35           | 1.35    |      |
|                 |                                  |  | 6.0                  | 1.8             | 1.8            | 1.8     |      |
| V <sub>OH</sub> | Minimum High-Level Output        | $V_{in} = V_{IH}$                                | 2.0                  | 1.9             | 1.9            | 1.9     | V    |
|                 | Voltage                          | $ I_{out}  \le 20 \mu\text{A}$                   | 4.5                  | 4.4             | 4.4            | 4.4     |      |
|                 |                                  |  | 6.0                  | 5.9             | 5.9            | 5.9     |      |
|                 |                                  | $V_{in} = V_{IH}$ $ I_{out}  \le 3.6 \text{ mA}$ | 3.0                  | 2.48            | 2.34           | 2.2     |      |
|                 |                                  | $ I_{out}  \le 6.0 \text{ mA}$                   | 4.5                  | 3.98            | 3.84           | 3.7     |      |
|                 |                                  | $ I_{out}  \le 7.8 \text{ mA}$                   | 6.0                  | 5.48            | 5.34           | 5.2     |      |
| V <sub>OL</sub> | Maximum Low-Level Output         | $V_{in} = V_{IL}$                                | 2.0                  | 0.1             | 0.1            | 0.1     | V    |
|                 | Voltage                          | $ I_{out}  \le 20 \mu\text{A}$                   | 4.5                  | 0.1             | 0.1            | 0.1     |      |
|                 |                                  |  | 6.0                  | 0.1             | 0.1            | 0.1     |      |
|                 |                                  | $V_{in} = V_{IL}$ $ I_{out}  \le 3.6 \text{ mA}$ | 3.0                  | 0.26            | 0.33           | 0.4     |      |
|                 |                                  | $ I_{out}  \le 6.0 \text{ mA}$                   | 4.5                  | 0.26            | 0.33           | 0.4     |      |
|                 |                                  | $ I_{out}  \le 7.8 \text{ mA}$                   | 6.0                  | 0.26            | 0.33           | 0.4     |      |
| l <sub>in</sub> | Maximum Input Leakage Current    | V <sub>in</sub> = V <sub>CC</sub> or GND         | 6.0                  | ±[0.1           | ±]1.0          | ±]1.0   | μΑ   |
| l <sub>OZ</sub> | Maximum Three-State Leakage      | Output in High-Impedance State                   | 6.0                  | ±[0.5           | ±[5.0          | ±[10    | μΑ   |
|                 | Current                          | $V_{in} = V_{IL}$ or $V_{IH}$                    |                      |                 |                |         |      |
|                 |                                  | V <sub>out</sub> = V <sub>CC</sub> or GND        |                      |                 |                |         |      |
| Icc             | Maximum Quiescent Supply Current | V <sub>in</sub> = V <sub>CC</sub> or GND         | 6.0                  | 4.0             | 40             | 160     | μΑ   |
|                 | (per Package)                    | $I_{out} = 0 \mu A$                              |                      |                 |                |         |      |

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### AC ELECTRICAL CHARACTERISTICS ( $C_L$ = 50 pF, Input $t_r$ = $t_f$ = 6.0 ns)

|                    |   |                 | Gu              | aranteed Li    | mit     |      |
|--------------------|---|-----------------|-----------------|----------------|---------|------|
| Symbol             | Parameter   | V <sub>CC</sub> | – 55 to<br>25°C | ≤ <b>85</b> °C | ≤ 125°C | Unit |
| t <sub>PLH</sub> , | Maximum Propagation Delay, Input A to Output Y                      | 2.0             | 90              | 115            | 135     | ns   |
| t <sub>PHL</sub>   | (Figures 1 and 3)   | 3.0             | 36              | 45             | 60      |      |
|                    |   | 4.5             | 18              | 23             | 27      |      |
|                    |   | 6.0             | 15              | 20             | 23      |      |
| t <sub>PLZ</sub> , | Maximum Propagation Delay, Output Enable to Y                       | 2.0             | 120             | 150            | 180     | ns   |
| t <sub>PHZ</sub>   | (Figures 2 and 4)   | 3.0             | 45              | 60             | 80      |      |
|                    |   | 4.5             | 24              | 30             | 36      |      |
|                    |   | 6.0             | 20              | 26             | 31      |      |
| t <sub>PZL</sub> , | Maximum Propagation Delay, Output Enable to Y                       | 2.0             | 90              | 115            | 135     | ns   |
| t <sub>PZH</sub>   | (Figures 2 and 4)   | 3.0             | 36              | 45             | 60      |      |
|                    |   | 4.5             | 18              | 23             | 27      |      |
|                    |   | 6.0             | 15              | 20             | 23      |      |
| t <sub>TLH</sub> , | Maximum Output Transition Time, Any Output                          | 2.0             | 60              | 75             | 90      | ns   |
| $t_{THL}$          | (Figures 1 and 3)   | 3.0             | 22              | 28             | 34      |      |
|                    |   | 4.5             | 12              | 15             | 18      |      |
|                    |   | 6.0             | 10              | 13             | 15      |      |
| C <sub>in</sub>    | Maximum Input Capacitance   | _               | 10              | 10             | 10      | pF   |
| C <sub>out</sub>   | Maximum 3-State Output Capacitance (Output in High-Impedance State) | -               | 15              | 15             | 15      | pF   |

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

|          |   | Typical @ 25°C, V <sub>CC</sub> = 5.0 V |    |
|----------|---|---|----|
| $C_{PD}$ | Power Dissipation Capacitance (Per Buffer)* | 30                                      | pF |

<sup>\*</sup>Used to determine the no-load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### **ORDERING INFORMATION**

| Device          | Package                | Shipping <sup>†</sup> |  |
|-----------------|------------------------|-----------------------|--|
| MC74HC125AN     | PDIP-14                |                       |  |
| MC74HC125ANG    | PDIP-14<br>(Pb-Free)   | 25 Units / Rail       |  |
| MC74HC125AD     | SOIC-14                |                       |  |
| MC74HC125ADG    | SOIC-14<br>(Pb-Free)   | 55 Units / Rail       |  |
| MC74HC125ADR2   | SOIC-14                |                       |  |
| MC74HC125ADR2G  | SOIC-14<br>(Pb-Free)   | 2500 / Tape & Reel    |  |
| MC74HC125ADT    | TSSOP-14*              | 0011 11 / 12 11       |  |
| MC74HC125ADTG   | TSSOP-14*              | 96 Units / Rail       |  |
| MC74HC125ADTR2  | TSSOP-14*              | 0500 / T              |  |
| MC74HC125ADTR2G | TSSOP-14*              | 2500 / Tape & Reel    |  |
| MC74HC125AF     | SOEIAJ-14              |                       |  |
| MC74HC125AFG    | SOEIAJ-14<br>(Pb-Free) | 50 Units / Rail       |  |
| MC74HC125AFEL   | SOEIAJ-14              |                       |  |
| MC74HC125AFELG  | SOEIAJ-14<br>(Pb-Free) | 2000 / Tape & Reel    |  |
| MC74HC126AN     | PDIP-14                |                       |  |
| MC74HC126ANG    | PDIP-14<br>(Pb-Free)   | 25 Units / Rail       |  |
| MC74HC126AD     | SOIC-14                |                       |  |
| MC74HC126ADG    | SOIC-14<br>(Pb-Free)   | 55 Units / Rail       |  |
| MC74HC126ADR2   | SOIC-14                |                       |  |
| MC74HC126ADR2G  | SOIC-14<br>(Pb-Free)   | 2500 / Tape & Reel    |  |
| MC74HC126ADTR2  | TSSOP-14*              |                       |  |
| MC74HC126ADTR2G | TSSOP-14*              |                       |  |
| MC74HC126AFEL   | SOEIAJ-14              |                       |  |
| MC74HC126AFELG  | SOEIAJ-14<br>(Pb-Free) | 2000 / Tape & Reel    |  |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>This package is inherently Pb-Free.

#### **SWITCHING WAVEFORMS**

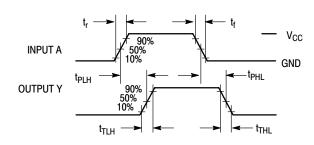


Figure 1.

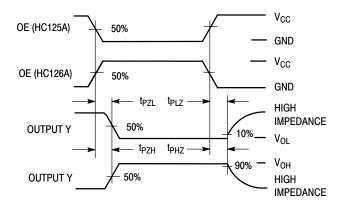
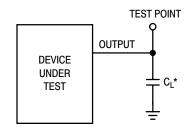


Figure 2.



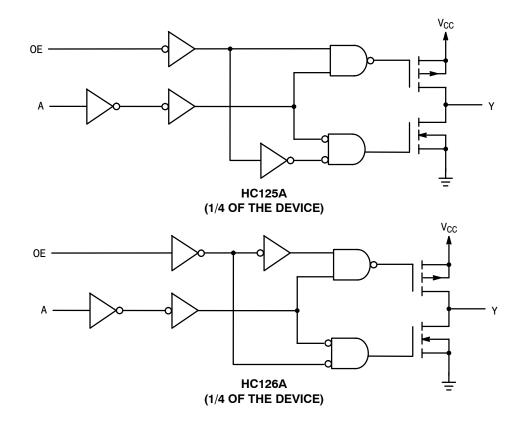
\*Includes all probe and jig capacitance

DEVICE UNDER TEST POINT  $\begin{array}{c|c} & & & & \\ &$ 

\*Includes all probe and jig capacitance

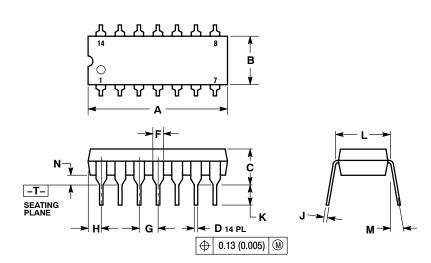
Figure 3. Test Circuit

Figure 4. Test Circuit



#### **PACKAGE DIMENSIONS**

PDIP-14 CASE 646-06 **ISSUE P** 

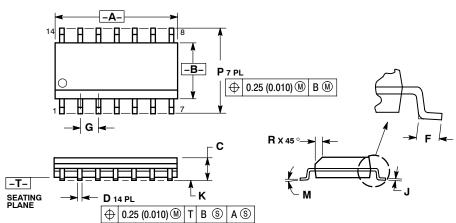


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

|     | INC       | HES   | MILLIM | IETERS |
|-----|-----------|-------|--------|--------|
| DIM | MIN       | MAX   | MIN    | MAX    |
| Α   | 0.715     | 0.770 | 18.16  | 19.56  |
| В   | 0.240     | 0.260 | 6.10   | 6.60   |
| С   | 0.145     | 0.185 | 3.69   | 4.69   |
| D   | 0.015     | 0.021 | 0.38   | 0.53   |
| F   | 0.040     | 0.070 | 1.02   | 1.78   |
| G   | 0.100 BSC |       | 2.54   | BSC    |
| Н   | 0.052     | 0.095 | 1.32   | 2.41   |
| J   | 0.008     | 0.015 | 0.20   | 0.38   |
| Κ   | 0.115     | 0.135 | 2.92   | 3.43   |
| ٦   | 0.290     | 0.310 | 7.37   | 7.87   |
| М   |           | 10 °  |        | 10 °   |
| N   | 0.015     | 0.039 | 0.38   | 1.01   |

#### PACKAGE DIMENSIONS

SOIC-14 CASE 751A-03 **ISSUE H** 



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

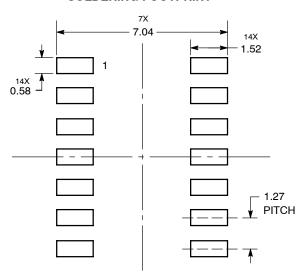
  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PEH SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

|     | MILLIMETERS |      | INC   | HES   |
|-----|-------------|------|-------|-------|
| DIM | MIN         | MAX  | MIN   | MAX   |
| Α   | 8.55        | 8.75 | 0.337 | 0.344 |
| В   | 3.80        | 4.00 | 0.150 | 0.157 |
| С   | 1.35        | 1.75 | 0.054 | 0.068 |
| D   | 0.35        | 0.49 | 0.014 | 0.019 |
| F   | 0.40        | 1.25 | 0.016 | 0.049 |
| G   | 1.27 BSC    |      | 0.050 | BSC   |
| J   | 0.19        | 0.25 | 0.008 | 0.009 |
| K   | 0.10        | 0.25 | 0.004 | 0.009 |
| M   | 0 °         | 7°   | 0 °   | 7 °   |
| Р   | 5.80        | 6.20 | 0.228 | 0.244 |
| R   | 0.25        | 0.50 | 0.010 | 0.019 |

#### **SOLDERING FOOTPRINT\***

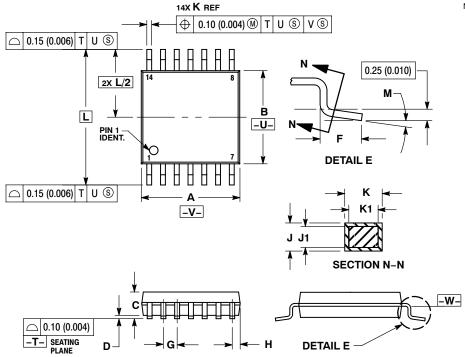


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

#### TSSOP-14 CASE 948G-01 **ISSUE B**

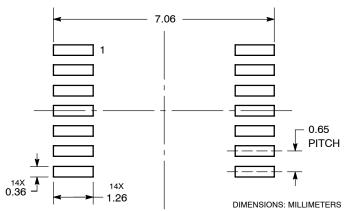


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - DIMENSIONING AND TOLEHANCING PEH ANSI Y14.5M, 1982.
     CONTROLLING DIMENSION: MILLIMETER.
     DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
     MOLD FLASH OR GATE BURRS SHALL NOT EVERED 14 16 (2008) DED SIDE.
  - EXCEED 0.15 (0.006) PER SIDE.

    4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
    INTERLEAD FLASH OR PROTRUSION SHALL
  - NOT EXCEED 0.25 (0.010) PER SIDE.
    5. DIMENSION K DOES NOT INCLUDE
    DAMBAR PROTRUSION. ALLOWABLE
    DAMBAR PROTRUSION SHALL BE 0.08 DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
    6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
    7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

|     | MILLIN   | IETERS | INC       | HES   |  |
|-----|----------|--------|-----------|-------|--|
| DIM | MIN      | MAX    | MIN       | MAX   |  |
| Α   | 4.90     | 5.10   | 0.193     | 0.200 |  |
| В   | 4.30     | 4.50   | 0.169     | 0.177 |  |
| С   |          | 1.20   |           | 0.047 |  |
| D   | 0.05     | 0.15   | 0.002     | 0.006 |  |
| F   | 0.50     | 0.75   | 0.020     | 0.030 |  |
| G   | 0.65 BSC |        | 0.026     | BSC   |  |
| Н   | 0.50     | 0.60   | 0.020     | 0.024 |  |
| J   | 0.09     | 0.20   | 0.004     | 0.008 |  |
| J1  | 0.09     | 0.16   | 0.004     | 0.006 |  |
| Κ   | 0.19     | 0.30   | 0.007     | 0.012 |  |
| K1  | 0.19     | 0.25   | 0.007     | 0.010 |  |
| L   | 6.40     | BSC    | 0.252 BSC |       |  |
| М   | 0 °      | 8 °    | 0 °       | 8 °   |  |

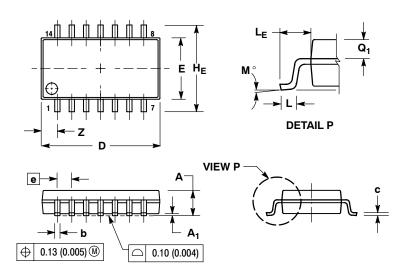
#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 **ISSUE A** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS D AND E DO NOT INCLUDE
  MOLD FLASH OR PROTRUSIONS AND ARE
  MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

|                | MILLIMETERS |       | INC   | HES   |
|----------------|-------------|-------|-------|-------|
| DIM            | MIN         | MAX   | MIN   | MAX   |
| Α              |             | 2.05  |       | 0.081 |
| A <sub>1</sub> | 0.05        | 0.20  | 0.002 | 0.008 |
| b              | 0.35        | 0.50  | 0.014 | 0.020 |
| С              | 0.10        | 0.20  | 0.004 | 0.008 |
| D              | 9.90        | 10.50 | 0.390 | 0.413 |
| Е              | 5.10        | 5.45  | 0.201 | 0.215 |
| е              | 1.27 BSC    |       | 0.050 | ) BSC |
| HE             | 7.40        | 8.20  | 0.291 | 0.323 |
| 0.50           | 0.50        | 0.85  | 0.020 | 0.033 |
| LE             | 1.10        | 1.50  | 0.043 | 0.059 |
| M              | 0 °         | 10°   | 0 °   | 10 °  |
| $Q_1$          | 0.70        | 0.90  | 0.028 | 0.035 |
| Z              |             | 1.42  |       | 0.056 |

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